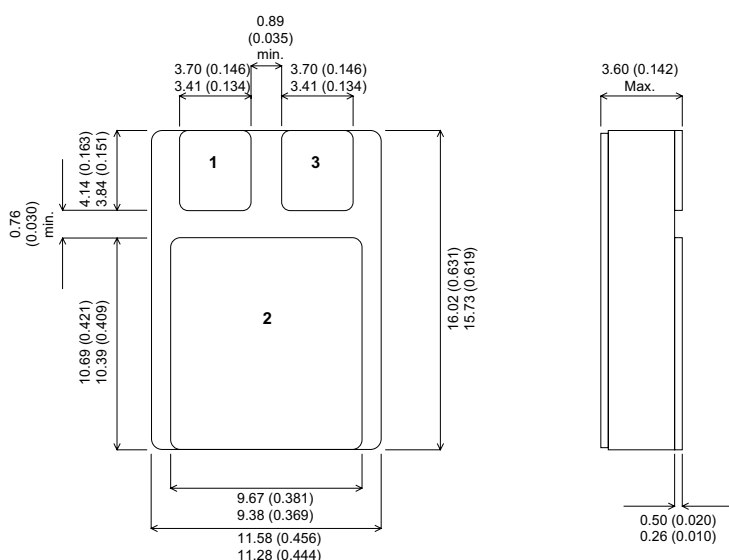


MECHANICAL DATA

Dimensions in mm (inches)


SMD 1

Pad 1 – Gate

Pad 2 – Drain

Pad 3 – Source

**N-CHANNEL
POWER MOSFET
FOR HI-REL
APPLICATIONS**
 V_{DSS} **100V**
 $I_{D(cont)}$ **11A**
 $R_{DS(on)}$ **0.19Ω**
FEATURES

- HERMETICALLY SEALED
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- SCREENING OPTIONS AVAILABLE
- ALL LEADS ISOLATED FROM CASE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current @ $T_{case} = 25^{\circ}C$	11A
I_D	Continuous Drain Current @ $T_{case} = 100^{\circ}C$	7A
I_{DM}	Pulsed Drain Current	44A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	45W
	Linear Derating Factor	0.36W/ $^{\circ}C$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to $150^{\circ}C$
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.8 $^{\circ}C/W$ max.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS							
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0	I _D = 1mA	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I _D = 1mA			0.1		V/°C
R _{DS(on)}	Static Drain – Source On–State Resistance	V _{GS} = 10V	I _D = 7A			0.19	Ω
		V _{GS} = 10V	I _D = 11A			0.22	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS}	I _D = 250μA	2		4	V
g _{fs}	Forward Transconductance	V _{DS} ≥ 15V	I _{DS} = 7A	3			S(̄v)
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0	V _{DS} = 0.8BV _{DSS}			25	μA
			T _J = 125°C			250	
I _{GSS}	Forward Gate – Source Leakage	V _{GS} = 20V				100	nA
I _{GSS}	Reverse Gate – Source Leakage	V _{GS} = –20V				-100	
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{GS} = 0			650		pF
C _{oss}	Output Capacitance	V _{DS} = 25V			240		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz			44		
Q _g	Total Gate Charge	V _{GS} = 10V I _D = 11A V _{DS} = 0.5BV _{DSS}		12.8		28.5	nC
Q _{gs}	Gate – Source Charge	I _D = 11A		1.0		6.3	nC
Q _{gd}	Gate – Drain (“Miller”) Charge	V _{DS} = 0.5BV _{DSS}		3.8		16.6	
t _{d(on)}	Turn–On Delay Time	V _{DD} = 50V I _D = 11A R _G = 7.5Ω				30	ns
t _r	Rise Time					75	
t _{d(off)}	Turn–Off Delay Time					40	
t _f	Fall Time					45	
SOURCE – DRAIN DIODE CHARACTERISTICS							
I _S	Continuous Source Current					11	A
I _{SM}	Pulse Source Current					43	
V _{SD}	Diode Forward Voltage	I _S = 11A T _J = 25°C V _{GS} = 0				1.5	V
t _{rr}	Reverse Recovery Time	I _S = 11A T _J = 25°C				300	ns
Q _{rr}	Reverse Recovery Charge	d _i / d _t ≤ 100A/μs V _{DD} ≤ 50V				3	μC
PACKAGE CHARACTERISTICS							
L _D	Internal Drain Inductance	(from 6mm down drain lead pad to centre of die)			8.7		nH
L _S	Internal Source Inductance	(from 6mm down source lead to centre of source bond pad)			8.7		